



Description

JMT P-channel Enhancement Mode Power MOSFET

Features

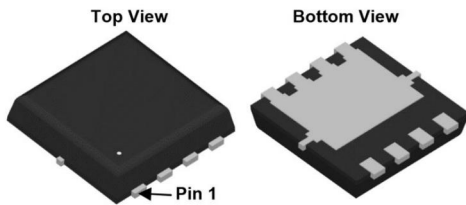
- $V_{DS} = -30V$, $I_D = -40A$
 $R_{DS(ON)} < 9.4m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 15.1m\Omega @ V_{GS} = -4.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free

Application

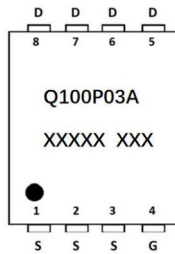
- PWM Applications
- Load Switch
- Power Management



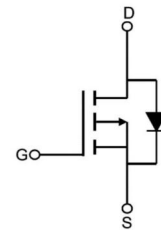
100% UIS TESTED!
100% ΔVds TESTED!



PDFN3x3-8L



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Outline	Package	Reel Size	Reel (pcs)	Per Carton (pcs)
Q100P03A	JMTQ100P03A	TAPING	PDFN3x3-8L	13"	5000	50000

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	-30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	-40
		$T_C = 100^\circ C$	-26
I_{DM}	Pulsed Drain Current ^{note1}	-160	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}	132	mJ
P_D	Power Dissipation	$T_C = 25^\circ C$	24
$R_{\theta JC}$	Thermal Resistance, Junction to Case	5.2	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} =0V	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} = -10V, I _D = -20A	-	7.5	9.4	mΩ
		V _{GS} = -4.5V, I _D = -10A	-	11.6	15.1	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -15V, V _{GS} =0V, f=1.0MHz	-	3766	-	pF
C _{oss}	Output Capacitance		-	437	-	pF
C _{rss}	Reverse Transfer Capacitance		-	343	-	pF
Q _g	Total Gate Charge	V _{DD} = -15V, I _D = -20A, V _{GS} = -10V	-	68	-	nC
Q _{gs}	Gate-Source Charge		-	11	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	14	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -15V, I _D = -30A, V _{GS} = -10V, R _{GEN} =2.4Ω	-	10	-	ns
t _r	Turn-on Rise Time		-	108	-	ns
t _{d(off)}	Turn-off Delay Time		-	87	-	ns
t _f	Turn-off Fall Time		-	86	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-40	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-160	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -30A	-	-	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: Starting T_J= 25°C, V_{DD}= -15V, V_{GS}= -10V, L= 0.5mH, R_G= 25Ω, I_{AS}= -23A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%



Typical Performance Characteristics

Figure 1: Output Characteristics

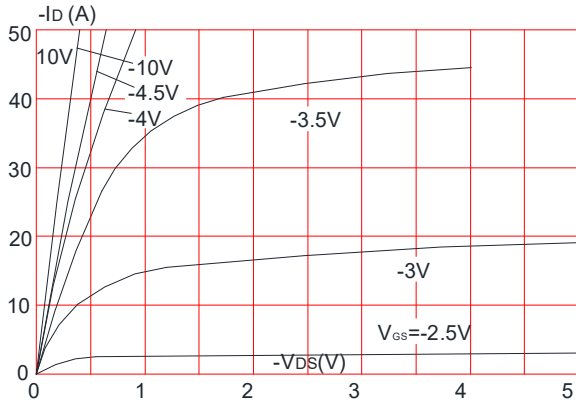


Figure 2: Typical Transfer Characteristics

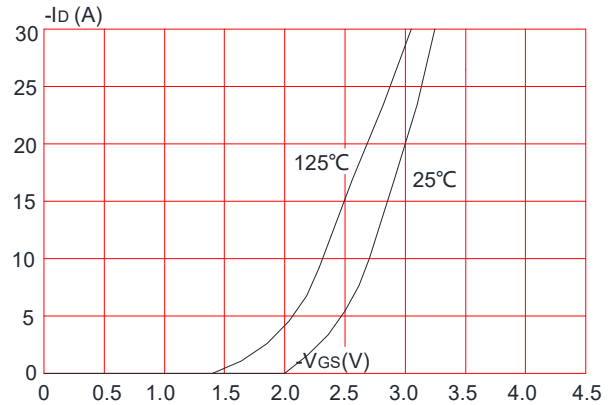


Figure 3: On-resistance vs. Drain Current

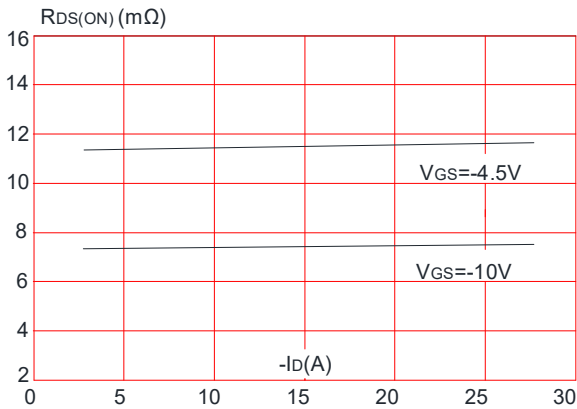


Figure 4: Body Diode Characteristics

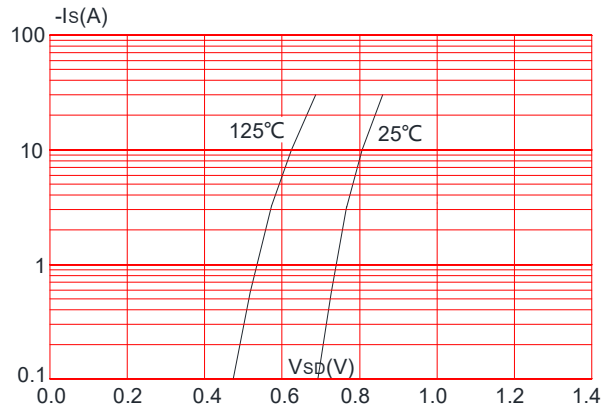


Figure 5: Gate Charge Characteristics

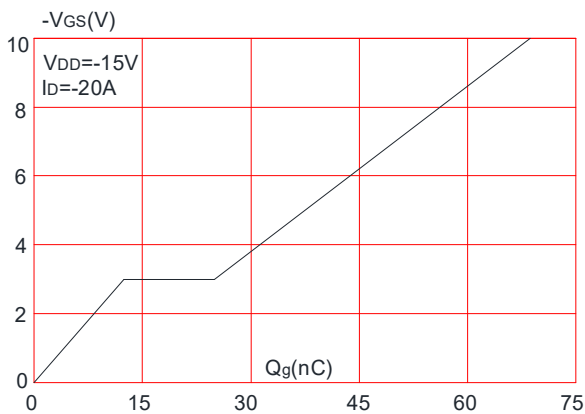
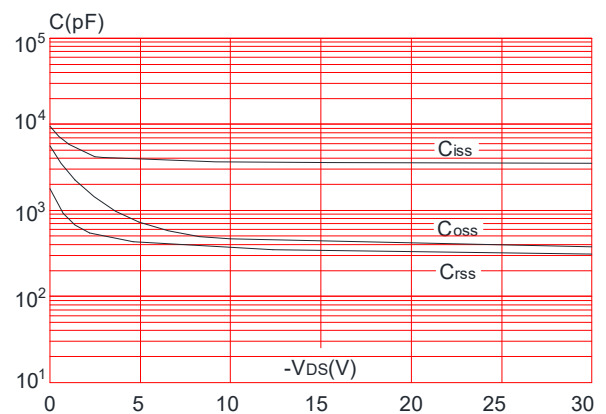


Figure 6: Capacitance Characteristics





JMTQ100P03A

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

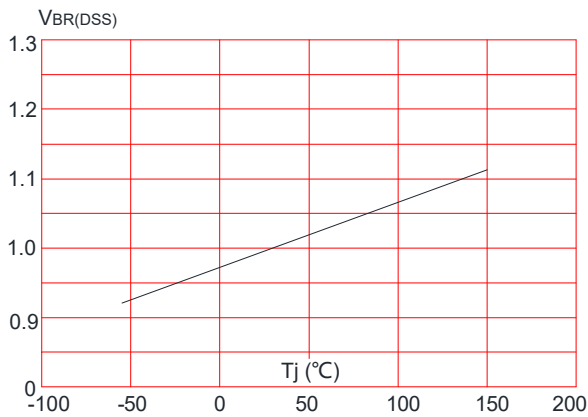


Figure 8: Normalized on Resistance vs. Junction Temperature

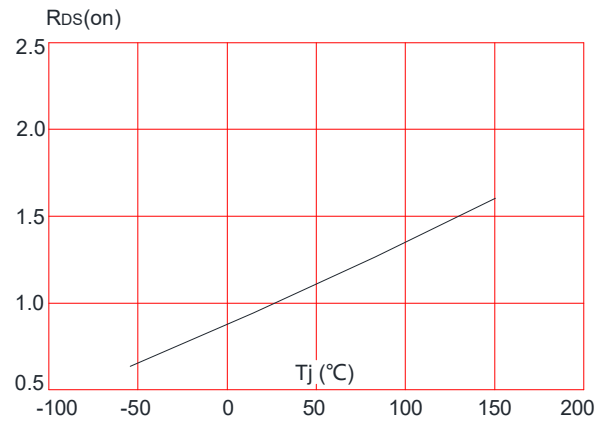


Figure 9: Maximum Safe Operating Area

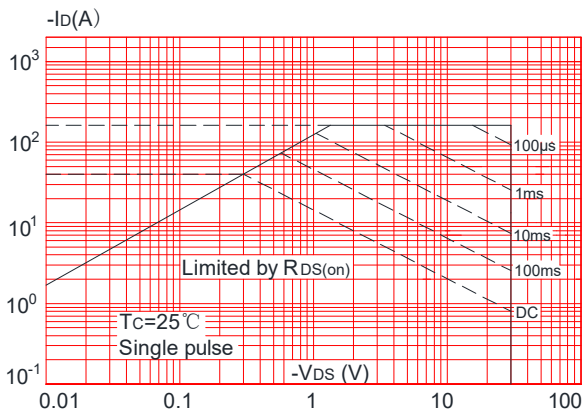


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

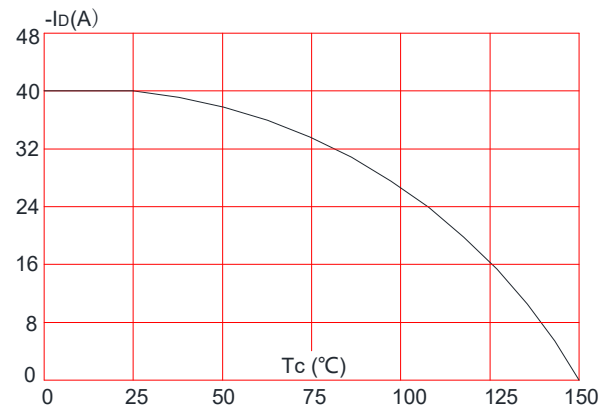
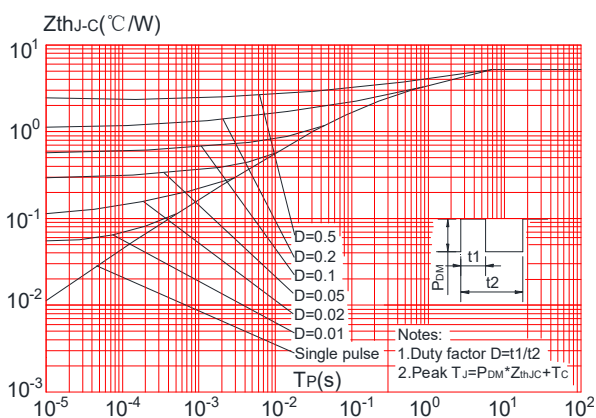


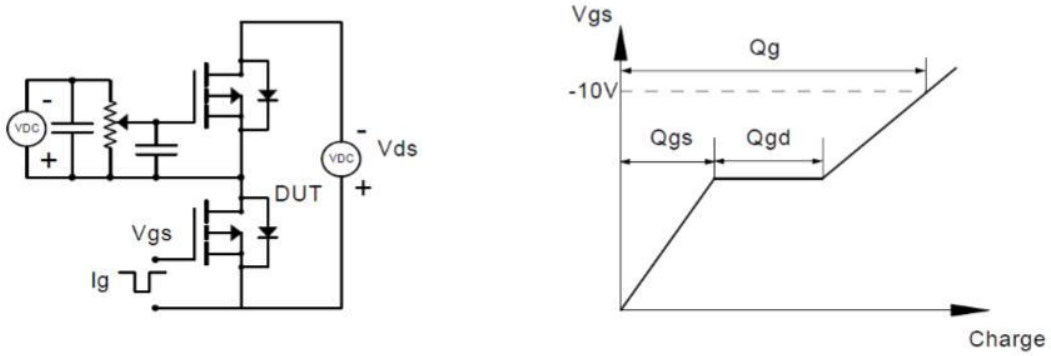
Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



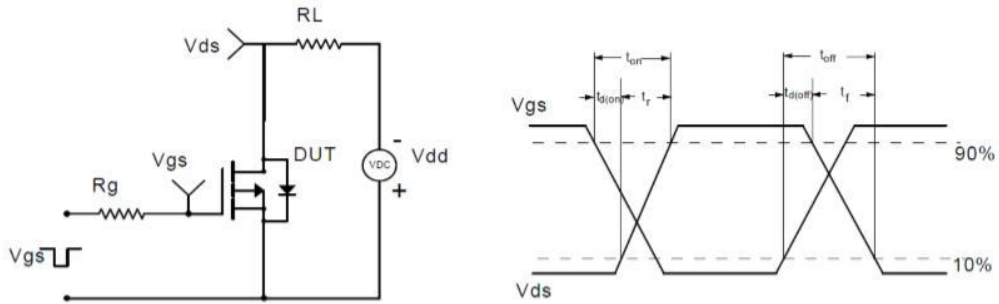


Test Circuit

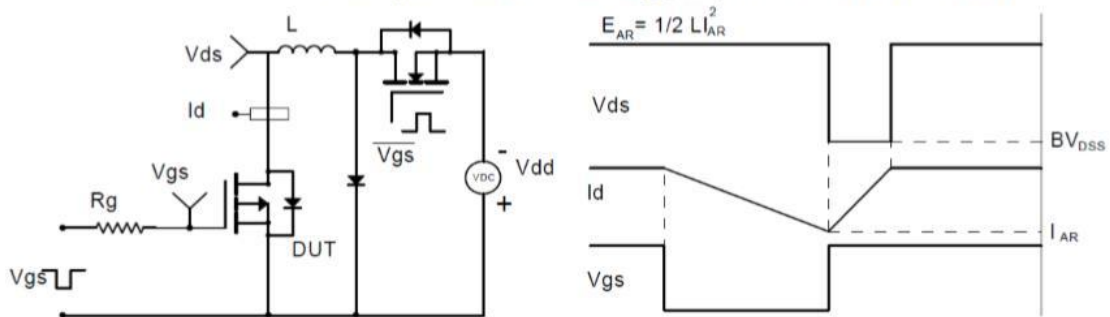
Gate Charge Test Circuit & Waveform



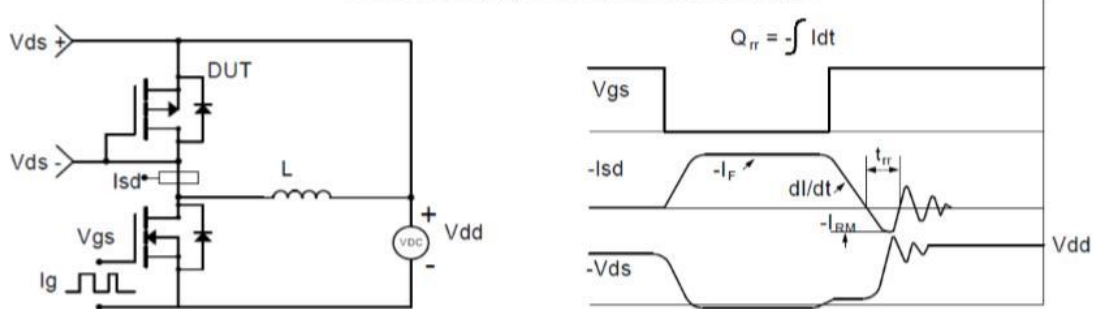
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

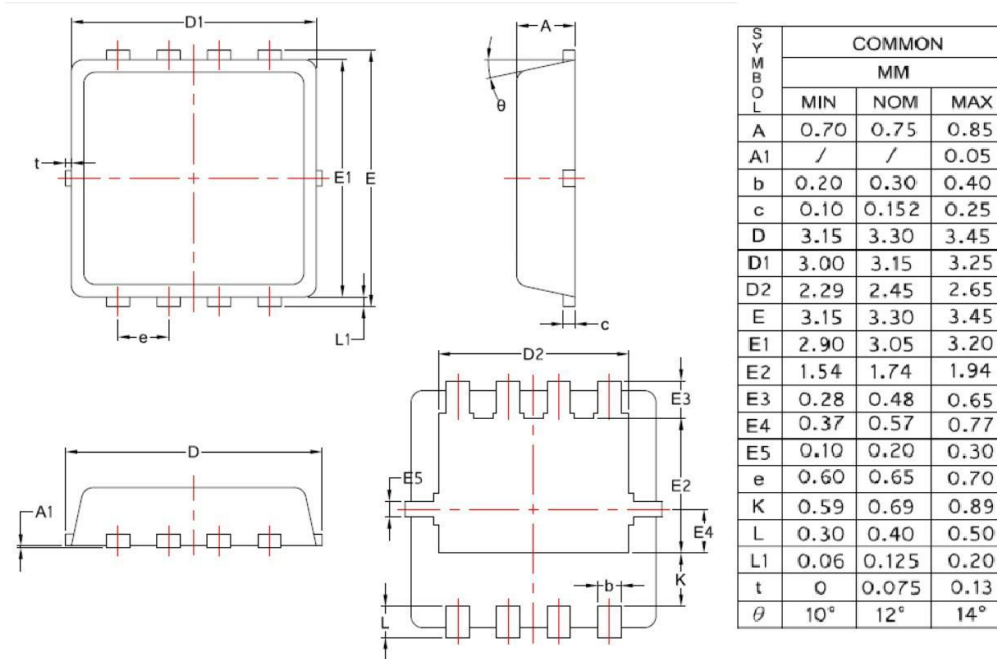


Diode Recovery Test Circuit & Waveforms

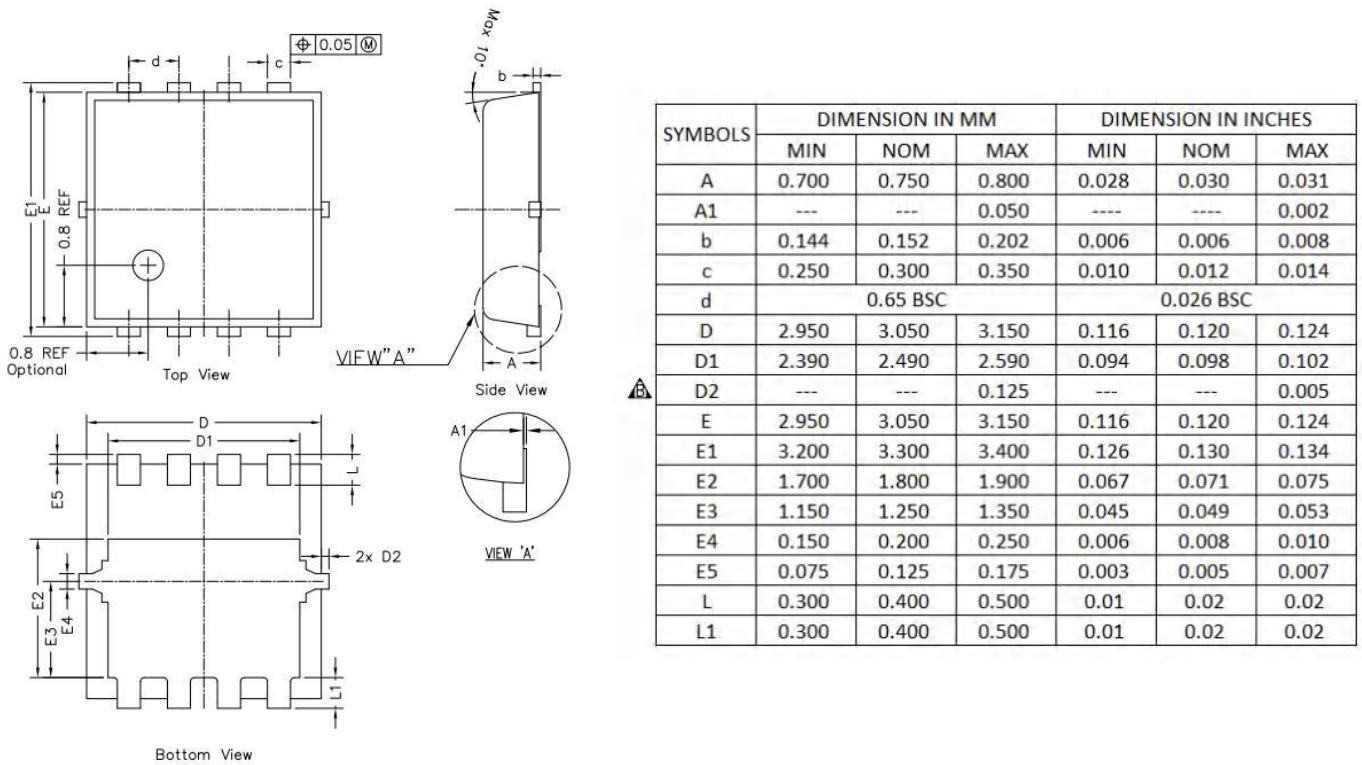




Package Mechanical Data-PDFN3x3-8L-Type A



Package Mechanical Data-PDFN3x3-8L-Type B






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